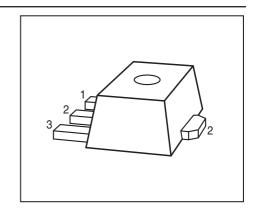


PNP Silicon AF Transistors

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type: BCX68 (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101







Туре	Marking	Pin Configuration			Package
BCX69-10	CF	1=B	2=C	3=E	SOT89
BCX69-16	CG	1=B	2=C	3=E	SOT89
BCX69-25	СН	1=B	2=C	3=E	SOT89

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V _{CEO}	20	V
Collector-base voltage	V_{CBO}	25	
Emitter-base voltage	V_{EBO}	5	
Collector current	I _C	1	Α
Peak collector current, $t_p \le 10 \text{ ms}$	I _{CM}	2	
Base current	I _B	100	mA
Peak base current	I _{BM}	200	
Total power dissipation-	P _{tot}	3	W
<i>T</i> _S = 114 °C			
Junction temperature	T_{i}	150	°C
Storage temperature	T _{stg}	-65 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 12	K/W

1

 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

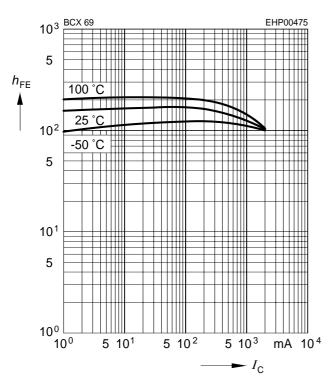
Parameter Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				i	•
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	20		-	V
$I_{\rm C}$ = 30 mA, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	$V_{(BR)CBO}$	25	-	-	
$I_{\rm C}$ = 10 μ A, $I_{\rm E}$ = 0					
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5	-	-	
$I_{\rm E}$ = 1 μ A, $I_{\rm C}$ = 0					
Collector-base cutoff current	I _{CBO}				μA
$V_{\text{CB}} = 25 \text{ V}, I_{\text{E}} = 0$		-	-	0.1	
$V_{\text{CB}} = 25 \text{ V}, I_{\text{E}} = 0 , T_{\text{A}} = 150$		-	-	100	
DC current gain ¹⁾	h _{FE}				-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 10 V		50	-	-	
$I_{\rm C}$ = 500 mA, $V_{\rm CE}$ = 1 V, BCX69-10		85	100	160	
$I_{\rm C}$ = 500 mA, $V_{\rm CE}$ = 1 V, BCX69-16		100	160	250	
$I_{\rm C}$ = 500 mA, $V_{\rm CE}$ = 1 V, BCX69-25		160	250	375	
$I_{\rm C}$ = 1 A, $V_{\rm CE}$ = 1 V		60	-	-	
Collector-emitter saturation voltage ¹⁾	V _{CEsat}	-	-	0.5	V
$I_{\rm C}$ = 1 A, $I_{\rm B}$ = 100 mA					
Base-emitter voltage ¹⁾	V _{BE(ON)}				
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 10 V		-	0.6	-	
$I_{\rm C}$ = 1 A, $V_{\rm CE}$ = 1 V		-	-	1	
AC Characteristics			•	•	,
Transition frequency	f _T	-	100	-	MHz
$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 5 V, f = 20 MHz					

¹Pulse test: $t < 300\mu s$; D < 2%



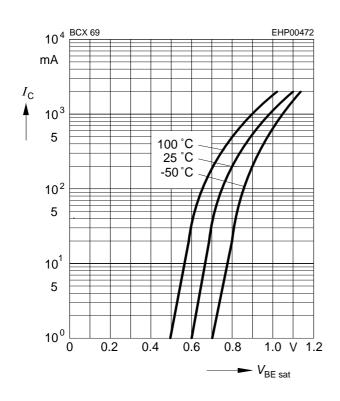
DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 1 \text{ V}$$



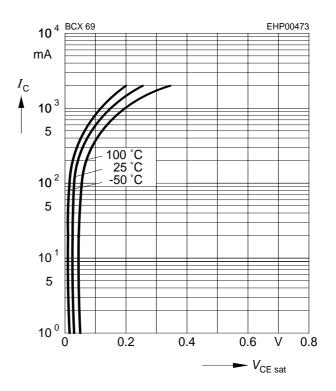
Base-emitter saturation voltage

$$I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$$



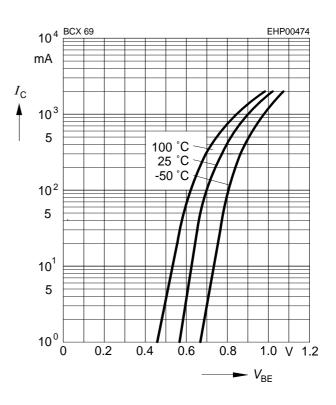
Collector-emitter saturation voltage

$$I_{\text{C}} = f(V_{\text{CEsat}}), h_{\text{FE}} = 10$$



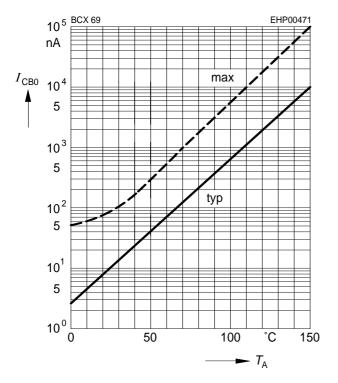
Collector current $I_{C} = f(V_{BE})$

$$V_{CE} = 1V$$

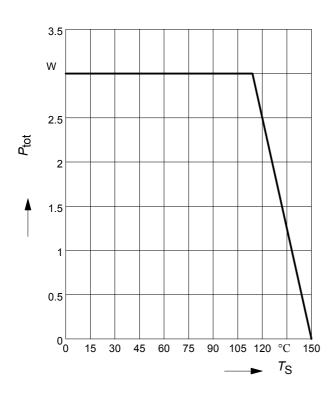




Collector cutoff current $I_{CBO} = f(T_A)$ $V_{CB} = 25 \text{ V}$

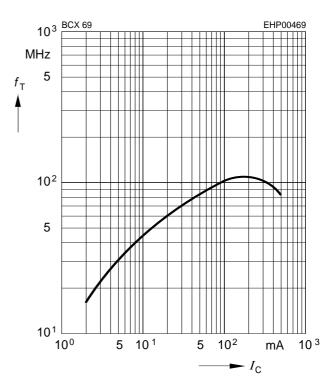


Total power dissipation $P_{tot} = f(T_S)$

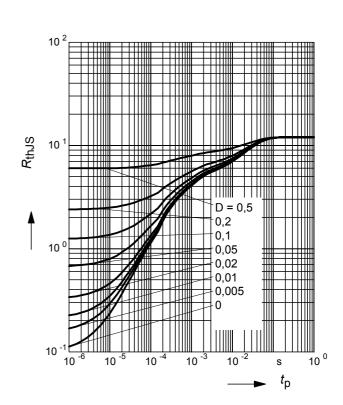


Transition frequency $f_T = f(I_C)$

$$V_{CE} = 5 \text{ V}$$



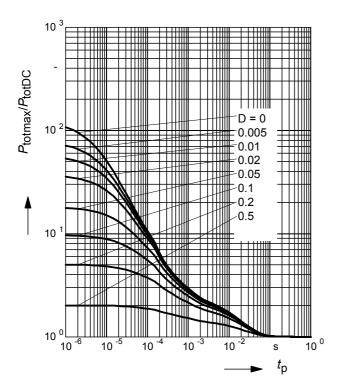
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

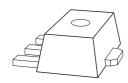
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$

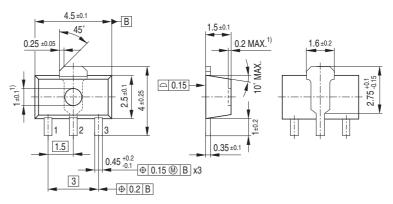


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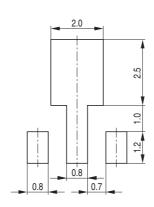
Package Outline



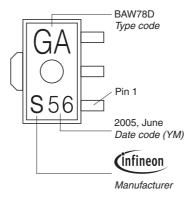


1) Ejector pin markings possible

Foot Print

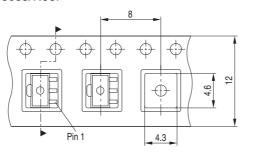


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 1.000 Pieces/Reel Reel ø330 mm = 4.000 Pieces/Reel



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